

**In the specification:**

Page 3, after line 21, amend the paragraph to read as follows:

“In the case of gas with a low ratio of carbon atoms to fluorine atoms (that is, C/F ratio), such as the aforementioned CHF<sub>3</sub> (or CF<sub>4</sub>), it is generally known that the quantity of F radicals in the plasma is large and the Si<sub>3</sub>N<sub>4</sub> or a resist will be easily etched. In contrast with this, in the case of gas with a high low C/F ratio, such as the aforementioned C<sub>4</sub>F<sub>8</sub>, the quantity of CF<sub>x</sub> radicals in the plasma is large; these CF<sub>x</sub> ~~radials~~ radicals are deposited on a film and function to prevent Si or Si<sub>3</sub>N<sub>4</sub> from reacting with the F radicals. It is also generally known that the result is that these films are difficult to etch.”

Page 5, after line 11, cancel the prior amendment and replace with the following paragraph:

“A feature of the present invention is to provide a semiconductor device manufacturing method the includes the steps of providing a semiconductor substrate having a lower electrically conducting layer thereon and an electrically insulating layer disposed over the electrically conducting layer, providing a gas etchant comprising a mixed gas of two different fluorocarbon gases, each of the fluorocarbon gases having a different ratio of carbon atoms to fluorine atoms, the fluorocarbon gas having the higher ratio of carbon atoms to fluorine atoms forming at least one half of the mixed gas and etching a connection hole through the electrically insulating layer in a single etching step to the electrically conducting layer using only the mixed gas as the etchant.”